

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (*Currently Amended*) A method for manufacturing a metal-oxide-semiconductor transistor, comprising:

forming a metal thin film and an isolation oxidation film on a semiconductor substrate, and selectively etching the isolation oxidation film such that the isolation oxidation film is left remaining only over a field oxidation film;

heat treating the semiconductor substrate to form silicide by the metal thin film in gate, source, and drain regions;

removing portions of the metal thin film that is not formed into silicide, ~~that is, removing unreacted metal thin film;~~

removing the isolation oxidation film left remaining on the field oxidation film; and

heat treating the semiconductor substrate in an oxygen environment to form the unreacted metal thin film remaining on the field oxidation film into a metal oxidation film.

2. (*Currently Amended*) The method of claim 1, wherein the metal thin film is formed by depositing a metal such as titanium and cobalt to a thickness of about 300 to 500Å.

3. (*Currently Amended*) The method of claim 1, wherein the silicide is formed by performing rapid thermal processing of the metal thin film in a nitrogen environment, at a temperature of about 700 to 800°C, and for about 20 to 40 seconds.

4. (*Currently Amended*) The method of claim 1, wherein following the formation of the metal oxidation film, rapid thermal processing is performed in a

nitrogen environment, at a temperature of about 850 to 950°C, and for about ~~15~~ 5 to 15 seconds.

5. (*Currently Amended*) The method of claim 1, wherein the isolation oxidation film is formed by performing deposition to a thickness of about 800 to 1200Å using plasma enhanced chemical vapor deposition.

6. (*Currently Amended*) The method of claim 1, wherein the metal oxidation film is formed by performing rapid thermal processing in an oxygen environment, at a temperature of about 700 to 800°C, and for about 20 to 40 seconds.

7. – 12. (*Cancelled*).